

Amendments to the Claims

1. (Currently Amended): A method of forming a phosphorus doped silicon dioxide-comprising layer, comprising:

~~positioning providing~~ a substrate within a deposition chamber; and introducing first and second vapor phase reactants in alternate and temporally separated pulses to the substrate within the chamber in a plurality of deposition cycles under conditions effective to deposit a phosphorus doped silicon dioxide-comprising layer on the substrate, one of the first and second vapor phase reactants being $\text{PO}(\text{OR})_3$ where R is hydrocarbyl, and an other of the first and second vapor phase reactants being $\text{Si}(\text{OR})_3\text{OH}$ where R is hydrocarbyl.

2. (Original): The method of claim 1 wherein the conditions comprise atomic layer deposition.

3. (Previously Presented): The method of silicon dioxide-comprising layer to have no more than 0.5 atomic percent phosphorus.

4. (Previously Presented): The method of claim 1 wherein the conditions are effective to form the silicon dioxide-comprising layer to have at least 1.0 atomic percent phosphorus.

5. (Previously Presented): The method of claim 1 being void of introducing any vapor phase reactant to the chamber other than said first and second vapor phase reactants in said forming of the phosphorus doped silicon dioxide-comprising layer.

6. (Original): The method of claim 1 comprising introducing another vapor phase reactant different from the first and second vapor phase reactants intermediate at least some of said separated pulses of the first and second vapor phase reactants.

7. (Currently Amended): The method of claim 6 wherein the another vapor phase reactant is ~~oxygen-containing~~ oxygen-containing.

8. (Original): The method of claim 7 wherein the another vapor phase reactant comprises O₃.

9. (Currently Amended): The method of claim 6 wherein the another vapor phase reactant is ~~boron-containing~~ boron-containing, the phosphorus doped silicon dioxide-comprising layer comprising boron.

10. (Original): The method of claim 1 wherein the R hydrocarbyl of the PO(OR)₃ contains only from one to five carbon atoms.

11. (Original): The method of claim 1 wherein the R hydrocarbyl of the Si(OR)₃OH contains only from one to five carbon atoms.

12. (Original): The method of claim 1 wherein the PO(OR)₃ comprises triethyl phosphate.

13. (Original): The method of claim 1 wherein the Si(OR)₃OH comprises tris(tert-butoxy)silanol.

14. (Original): The method of claim 1 wherein the PO(OR)₃ comprises triethyl phosphate, and wherein the Si(OR)₃OH comprises tris(tert-butoxy)silanol.

15. (Original): The method of claim 1 wherein the conditions comprise a temperature from about 50°C to about 500°C.

16. (Original): The method of claim 15 wherein the conditions comprise a temperature from about 100°C to about 300°C.

17. (Original): The method of claim 1 wherein the conditions comprise a pressure from about 10⁻⁷ Torr to about 10 Torr.

18. (Original): The method of claim 1 wherein the conditions comprise plasma generation of at least one of the first and second reactants.

19. (Original): The method of claim 1 wherein the conditions are void of plasma generation of the first and second reactants.

20. (Original): The method of claim 1 comprising purging the chamber with an inert gas intermediate the separated pulses.

21. (Previously Presented): The method of claim 1 being void of aluminum on the substrate in said forming of the phosphorus doped silicon dioxide-comprising layer.

22. (Currently Amended): The method of claim 1 being void of introducing any vapor phase aluminum-containing aluminum-containing reactant to the chamber in said forming of the phosphorus doped silicon dioxide-comprising layer.

23. (Currently Amended): A method of forming a phosphorus doped silicon dioxide-comprising layer, comprising:

positioning providing a substrate within a deposition chamber;

chemisorbing a first species to a surface of the substrate to form a first species monolayer onto the surface within the chamber from a first vapor phase reactant comprising $\text{PO}(\text{OR})_3$, where R is hydrocarbyl;

contacting the chemisorbed first species with a second vapor phase reactant comprising $\text{Si}(\text{OR})_3\text{OH}$, where R is hydrocarbyl, to form a monolayer comprising Si and O; and

successively repeating chemisorbing with the first species and contacting the chemisorbed first species with the second reactant under conditions effective to deposit a phosphorus doped silicon dioxide-comprising layer on the substrate.

24. (Original): The method of claim 23 wherein the substrate surface to which the first species is at least first chemisorbed is provided to be an hydroxylated surface.

25. (Previously Presented): The method of claim 23 wherein the conditions are effective to form the silicon dioxide-comprising layer to have no more than 0.5 atomic percent phosphorus.

26. (Previously Presented): The method of claim 23 wherein the conditions are effective to form the silicon dioxide-comprising layer to have at least 1.0 atomic percent phosphorus.

27. (Previously Presented): The method of claim 24 being void of introducing any vapor phase reactant to the chamber other than said first and second vapor phase reactants at least after providing the hydroxylated surface in said forming of the phosphorus doped silicon dioxide-comprising layer.

28. (Original): The method of claim 23 comprising introducing another vapor phase reactant different from the first and second vapor phase reactants intermediate at least some of said repeated chemisorbings and contactings.

29. (Currently Amended): The method of claim 28 wherein the another vapor phase reactant is ~~oxygen-containing~~ oxygen-containing.

30. (Original): The method of claim 29 wherein the another vapor phase reactant comprises O₃.

31. (Currently Amended): The method of claim 28 wherein the another vapor phase reactant is ~~boron-containing~~ boron-containing, the phosphorus doped silicon dioxide-comprising layer comprising boron.

32. (Original): The method of claim 23 wherein the R hydrocarbyl of the PO(OR)₃ contains only from one to five carbon atoms.

33. (Original): The method of claim 23 wherein the R hydrocarbyl of the Si(OR)₃OH contains only from one to five carbon atoms.

34. (Original): The method of claim 23 wherein the PO(OR)₃ comprises triethyl phosphate.

35. (Original): The method of claim 23 wherein the Si(OR)₃OH comprises tris(tert-butoxy)silanol.

36. (Original): The method of claim 23 wherein the PO(OR)₃ comprises triethyl phosphate, and wherein the Si(OR)₃OH comprises tris(tert-butoxy)silanol.

37. (Original): The method of claim 23 comprising purging the chamber with an inert gas intermediate said repeated chemisorbings and contactings.

38. (Currently Amended): The method of claim 23 being void of aluminum on the substrate in said forming of the phosphorus doped silicon dioxide comprising silicon dioxide-comprising layer.

39. (Currently Amended): The method of claim 23 being void of introducing any vapor phase aluminum containing reactant to the chamber in said forming of the phosphorus doped ~~silicon dioxide comprising~~ silicon dioxide-comprising layer.

40. (Currently Amended): The method of claim 23 comprising depositing the phosphorus doped ~~silicon dioxide comprising~~ silicon dioxide-comprising layer within semiconductive material isolation trenches formed in the substrate.

Claims 41-58 (Canceled).

59. (Currently Amended): The method of claim 1 comprising forming said phosphorus doped silicon dioxide-comprising layer to be of uniform composition.

60. (Currently Amended): The method of claim 23 comprising forming said phosphorus doped silicon dioxide-comprising layer to be of uniform composition.